

*Amended*  
forming an embedded conductive layer comprising an organic resin to cover said insulating layer and said opening;

etching or polishing said embedded conductive layer to expose a portion of the insulating layer; and

forming a second conductive layer on said insulating layer and said embedded conductive layer.

*B'*  
2. (Amended) A method for producing a semiconductor device comprising:

forming a first conductive layer;

forming an insulating layer over said first conductive layer;

forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;

forming an oxide conductive layer by a spin coating method to cover said insulating layer and said opening;

etching or polishing said oxide conductive layer to make a state in that only said opening is filled with said oxide conductive layer; and

forming a second conductive layer on said insulating layer and said oxide conductive layer.

3. (Amended) A method for producing a semiconductor device comprising:

forming an active layer of a transistor;

forming an insulating layer over said active layer;

forming an opening in said insulating layer to expose a portion of the active layer at a bottom of said opening;

forming an embedded conductive layer comprising a black colored material to cover said insulating layer and said opening wherein the embedded conductive layer contacts the active layer in the opening;

*Amended  
but!* *7*

forming a transparent conductive layer on said embedded conductive layer;  
patterning said transparent conductive layer to form a transparent pixel electrode.

*B'*

4. (Amended) A method for producing a semiconductor device comprising:  
forming a first conductive layer;  
forming an insulating layer over said first conductive layer;  
forming an opening in said insulating layer to expose said first conductive layer at a  
bottom of said opening;  
forming an oxide conductive layer by a spin coating method, to cover said insulating  
layer and said opening;  
forming a second conductive layer on said oxide conductive layer;  
patterning said second conductive layer to a desired pattern, and  
etching said oxide conductive layer by using said second conductive layer as a mask in a  
self alignment manner.

5. (Amended) A method for producing a semiconductor device according to  
claim 1, wherein said embedded conductive layer comprises an organic resin film containing a  
conductive material dispersed therein.

*Amended  
but!* *7*

*B2*

14. (Amended) A method for producing a semiconductor device comprising:  
forming a first conductive layer;  
forming an insulating layer over said first conductive layer;  
forming an opening in said insulating layer to expose said first conductive layer at a  
bottom of said opening;  
forming a second conductive layer comprising a conductive oxide to cover said insulating  
layer and said opening;  
polishing said second conductive layer by employing a chemical mechanical polishing;  
and

*Cont'd*  
forming a third conductive layer on said insulating layer and said second conductive layer,  
wherein said third conductive layer is reflective.

*B2*  
15. (Amended) A method for producing a semiconductor device comprising:  
forming an active layer of a transistor;  
forming an insulating layer over the active layer;  
forming an opening in said insulating layer to expose a portion of the active layer at a bottom of said opening;  
forming a black colored conductive layer to cover said insulating layer and said opening;  
polishing said black colored conductive layer by employing a chemical mechanical polishing; and  
forming a second conductive layer on said insulating layer and said oxide conductive layer, wherein said second conductive layer is transparent.

*B3*  
18. (Amended) A method for producing a semiconductor device according to claim 14, wherein said conductive oxide comprises a metal oxide.

20. (Amended) A method for producing a semiconductor device according to claim 1, 2, 3, 4, 14 or 15, wherein said semiconductor device is a cellular phone.

*B4*  
21. (Amended) A method for producing a semiconductor device according to claim 1, 2, 3, 4, 14 or 15, wherein said semiconductor device is a camcorder.

22. (Amended) A method for producing a semiconductor device according to claim 1, 2, 3, 4, 14 or 15, wherein said semiconductor device is a portable computer.

23. (Amended) A method for producing a semiconductor device according to claim 1, 2, 3, 4, 14 or 15, wherein said semiconductor device is a head mounted display.

B4 24. (Amended) A method for producing a semiconductor device according to claim 1, 2, 3, 4, 14 or 15, wherein said semiconductor device is a rear type projector.

25. (Amended) A method for producing a semiconductor device according to claim 1, 2, 3, 4, 14 or 15, wherein said semiconductor device is a front type projector.

26. (Amended) A method for producing a semiconductor device according to claim 1, 2, 3, 4, 14 or 15, wherein said semiconductor device is an EL display device.

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Please add new claims 27-29 as follows:

--27. The method according to claim 1 wherein an exposed surface of the insulating layer is flush with the embedded conductive layer.

B5/C3 28. A method for producing a semiconductor device comprising:  
forming a first conductive layer;  
forming an insulating layer comprising an organic resin over said first conductive layer;  
forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;  
forming an embedded conductive layer comprising an organic resin to cover said insulating layer and said opening;  
removing a portion of said embedded conductive layer to expose a portion of the insulating layer; and  
forming a second conductive layer on said insulating layer and said embedded conductive layer.